

# Modelling signal digitisation for test calorimeters: the CALICE experience

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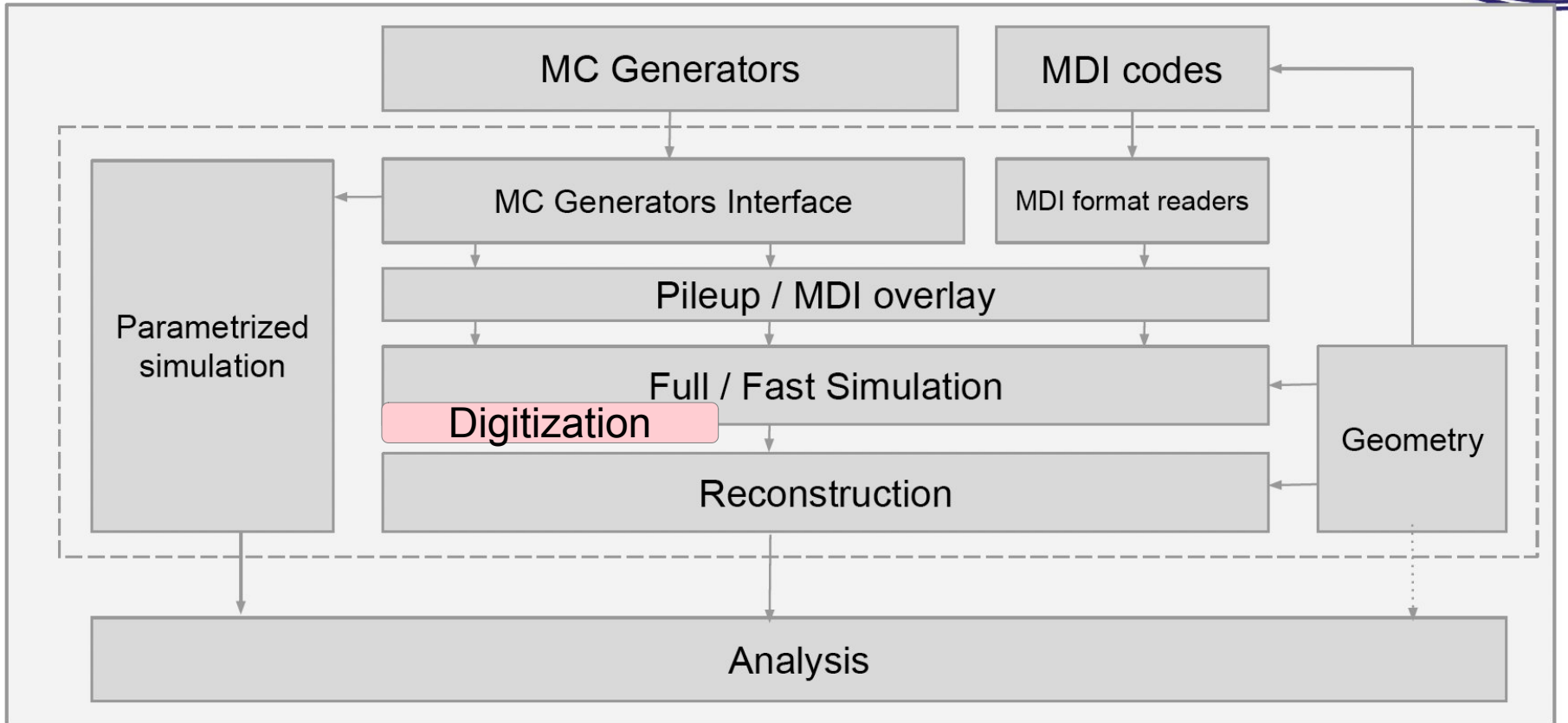
*LIR*



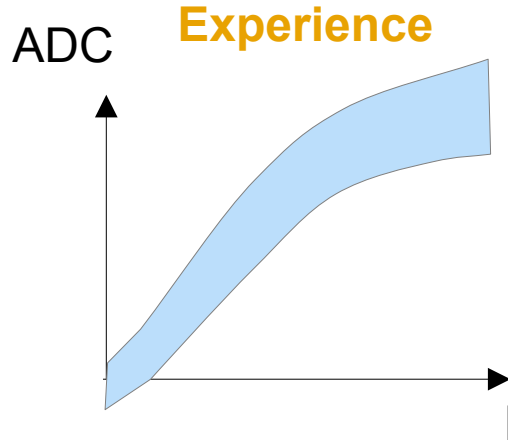
**FCC Week, 23-26/06/2023, Krakow**  
**→ Calo5D 1<sup>st</sup> F2F, 03/12/2024, KIT**



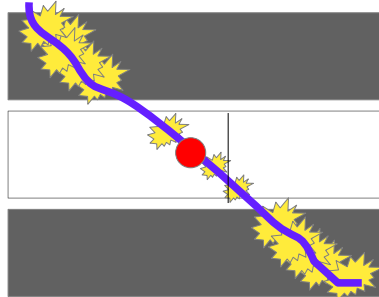
# What is digitization ?



# Problems:

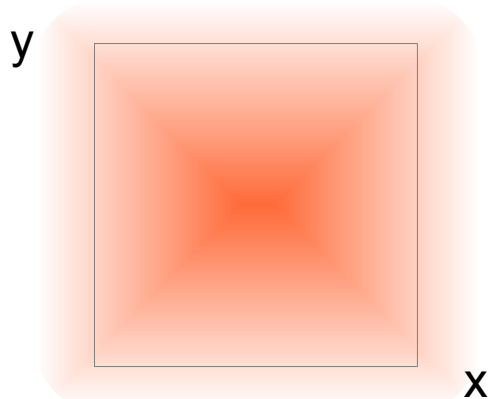
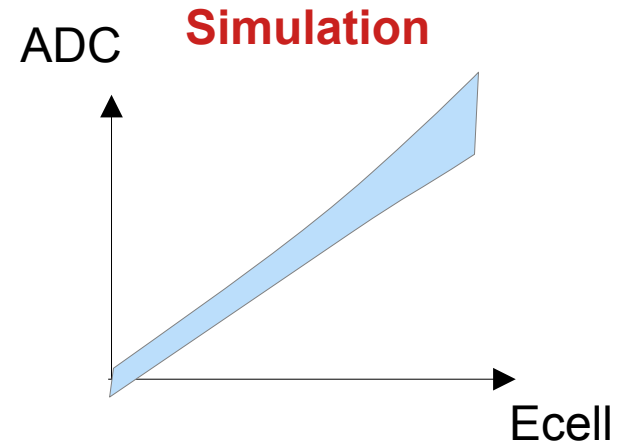


**E-t :**  
Saturations  
non-linearities  
(sensor, elec)  
Statistics  
Noise  
Thresholds



Sampling calorimeters

**E-t**  
Physics list  
Thresholds  
Steps



**Mapping**  
(in)Efficiency  
X-talk



**Mapping**  
Signal sharing

## in-cell non-linear effects

- Geometric efficiency, losses

## ALL

- Field / Efficiency maps
- Saturation
  - Scint: Birk's law
  - Gas
- SiPM: stat / inefficiencies
- Non-poissonian statistics
  - Si, IAr : Fano factor

## Electronics non-linearities

- Energy
  - LE : (Electronics) Noises, Threshold effects
  - HE: Saturation
- Time
  - Time-slew (method dependant : ToA, CFD, Shaping)
  - Precision

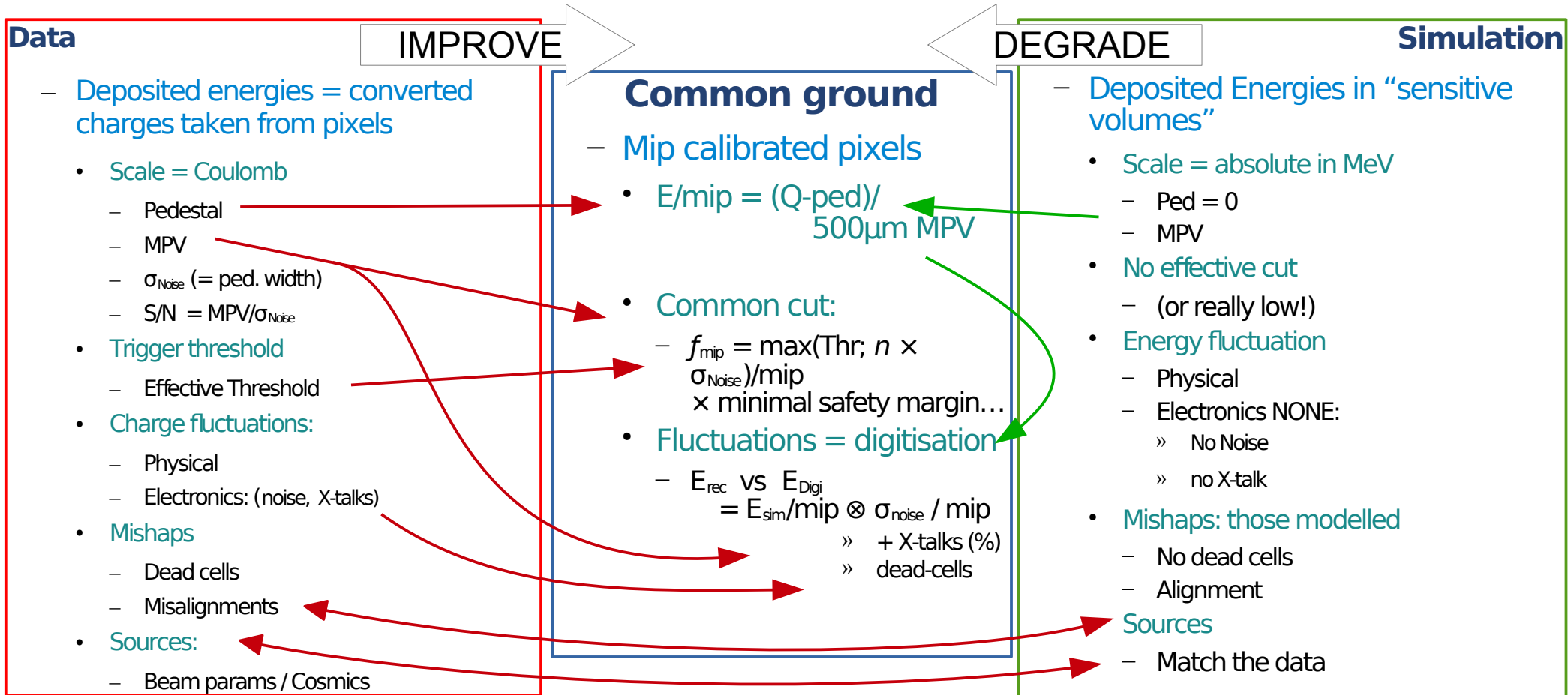
## Inter-cell

- X-talk
  - SDHCAL = multiplicity

## Pile-ups

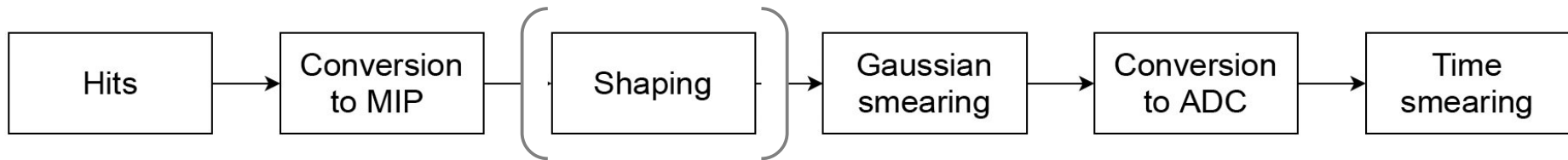
- Multiple hits
  - Time precision

# Data vs Simulation (Silicon example)



# Digitization: $E, t$ space

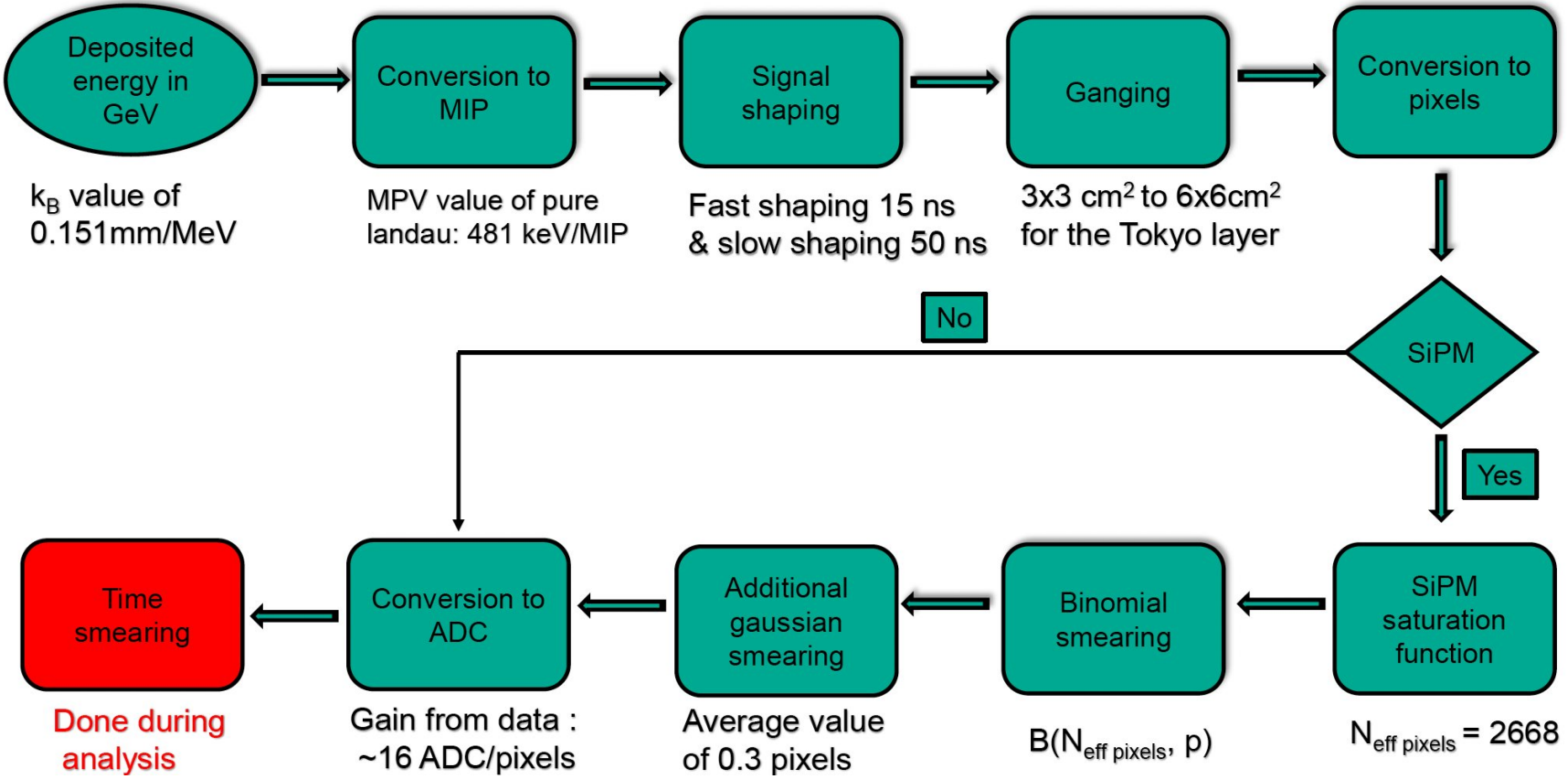
Raw simulation  $\Rightarrow$  info. resembling detector output, including readout effects



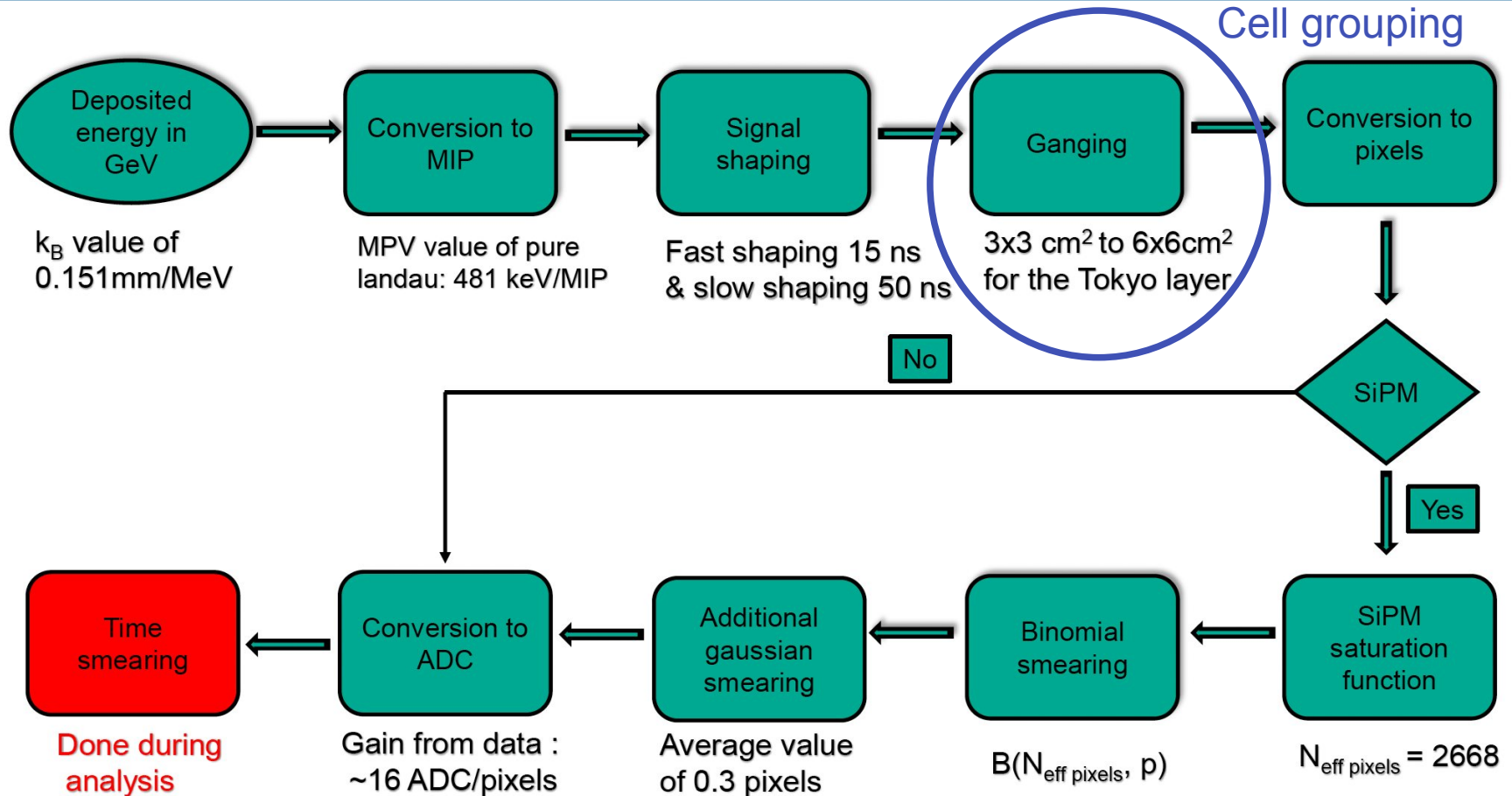
- Hits: starting point from raw simulation.
- Map energy deposited to MIP scale.
- Simulate pulse shaping in the readout electronics + saturation effects.
- Add smearing: noise term in detector cells/readout.
- Conversion to ADC, time smearing (tbd)
- (Masking at any point.)

# AHCAL Digi

Light yield determined from data



# Scint. Digi → ScECAL & AHCAL





# Scintillator's

## Deposited energy in GeV & conversion to MIP

Simulations of energy depositions in scintillators have to account for quenching effects giving rise to non-linear light yield per unit length ( $dL/dx$ ) at high ionization densities ( $dE/dx$ )

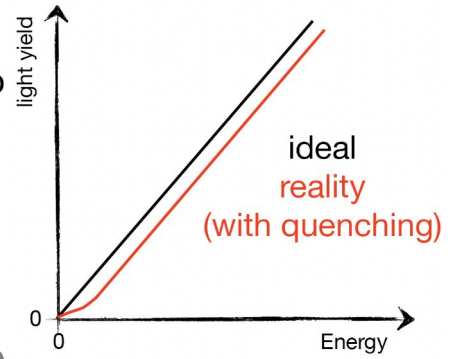
- Birks' law describes this effect with:

$$\frac{dL}{dx} = \frac{\left(S * \frac{dE}{dx}\right)}{1 + k_B * \frac{dE}{dx}}$$

- The AHCAL simulations use the Geant4 implementation of Birks' law with a Birks coefficient of  $k_B = 0.151 \text{ mm/MeV}$  [https://agenda.linearcollider.org/event/4776/contributions/19855/attachments/16078/26247/CALICE\\_Birks.pdf](https://agenda.linearcollider.org/event/4776/contributions/19855/attachments/16078/26247/CALICE_Birks.pdf)

MC Production and AHCAL Digitization | Olin Pinto, 30/06/2020

Alexander Tadday - CALICE Meeting 23.09.2010



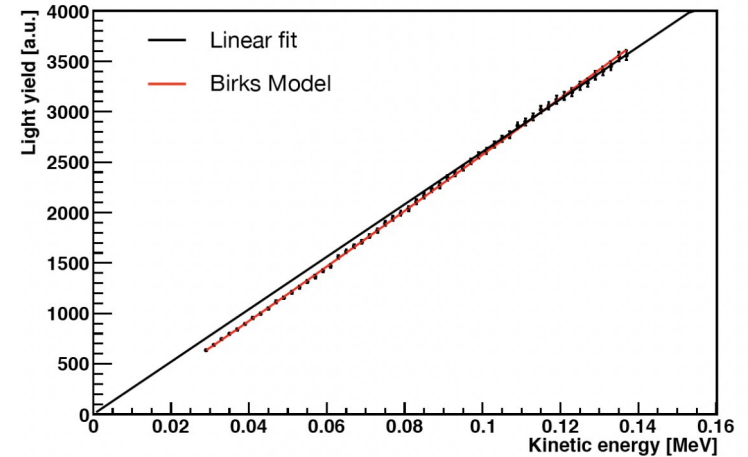
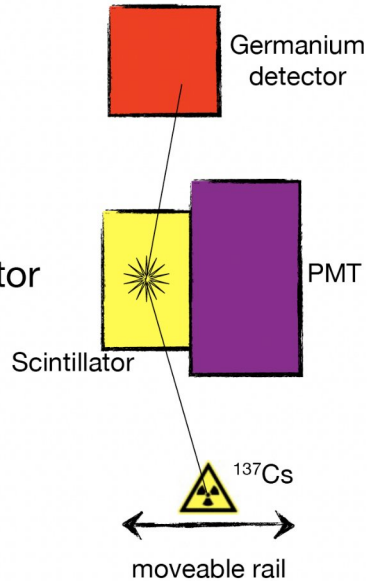
“Digi in G4”  
- Birk's law  
- (Light tracking)

**Depends on**  
- Scintillator type  
- Simulation step size

# Experimental Setup (MPIK Heidelberg)

- PMT measures light yield
- Germanium detector measures Energy of Compton scattered photon  $E_{Ge}$
- Coincidence trigger PMT and Ge-detector
- Measured energy range of electrons  $\sim 30 - 140$  keV
- Thanks to Christoph Aberle and Stefan Wagner for the ability to use the setup
- Detailed setup description in [1]

$$E_{e^-} = 662 \text{ keV} - E_{Ge}$$



Fit function:

$$LY \approx \sum_{i=1}^{R/\delta x} \frac{S \cdot \frac{dE}{dx}(E_i)}{1 + kB \cdot \frac{dE}{dx}(E_i)} \delta x$$

Small step-size:

$$\frac{dE}{dx}(E_1) \frac{dE}{dx}(E_2) \dots \frac{dE}{dx}(E_8) \rightarrow LY_1$$

Long step-size:

$$\frac{dE}{dx}(E_1) \rightarrow LY_2$$

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## Data generation

Particle type (e.g. proton)  
 $kB = 0.0151 \text{ cm/MeV}$   
 $S = 29807 \text{ a.u.}$



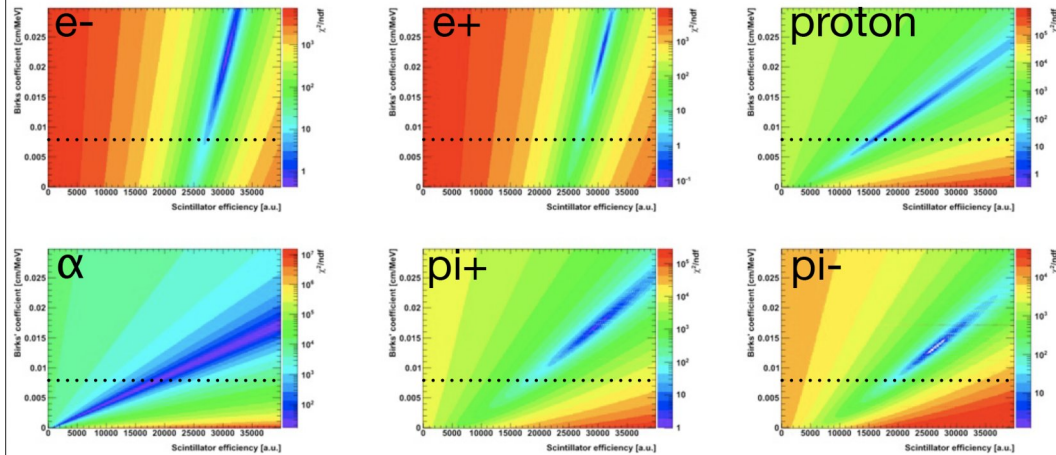
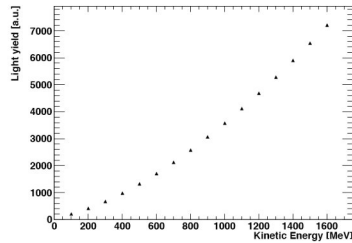
**GEANT4**  
*small step-size ( $\alpha, \rho$ )*  
*large production cut  $P_{cut}$*

chi squared distribution

GEANT4  
 default  $\alpha, \rho, P_{cut}$



“artificial”  
 data set

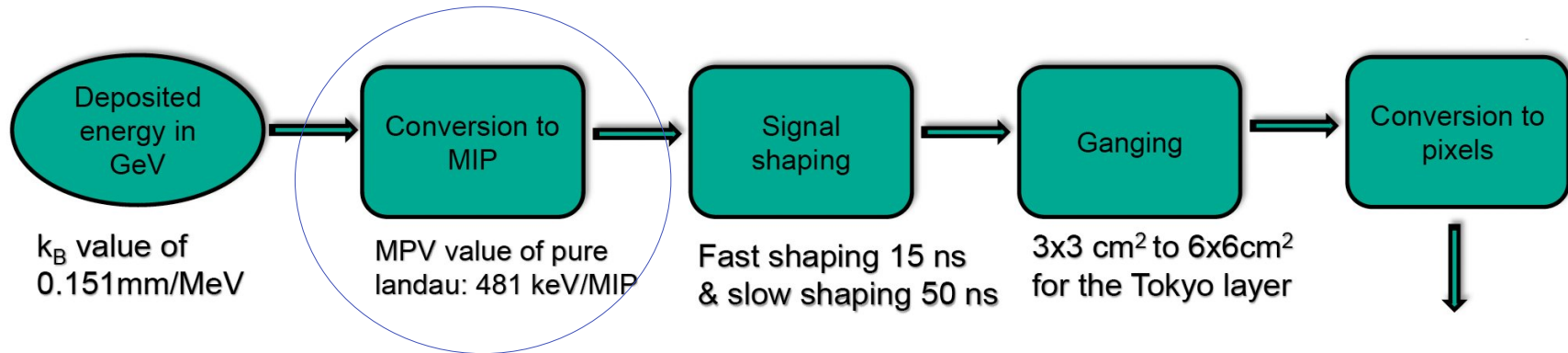


Different possibilities to combine results:  
 - Common  $kB, S$  for all particles  
 - Particle specific  $kB$ , but common  $S$

..... current  $kB$   
 $0.007943 \text{ cm/MeV}$

Alexander Taddy - CALICE Meeting 23.09.2010

# AHCAL Scintillator's



## Deposited energy in GeV & conversion to MIP

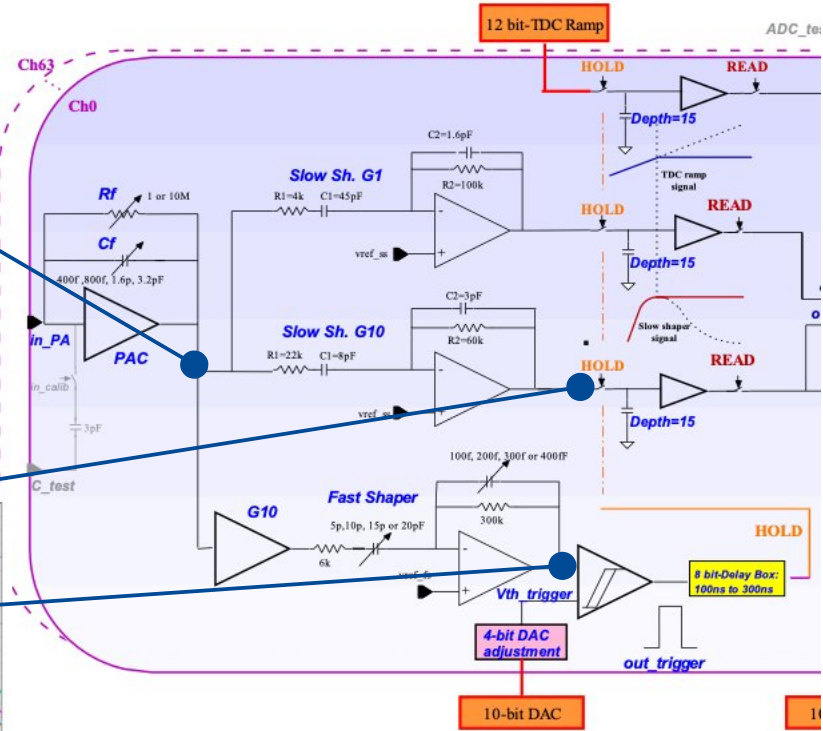
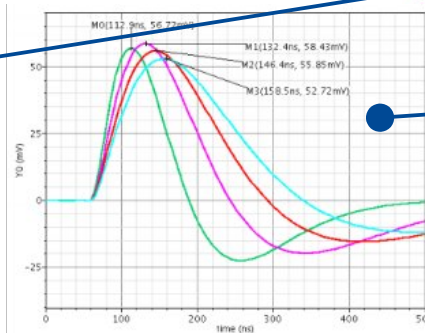
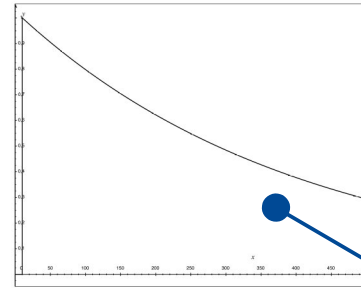
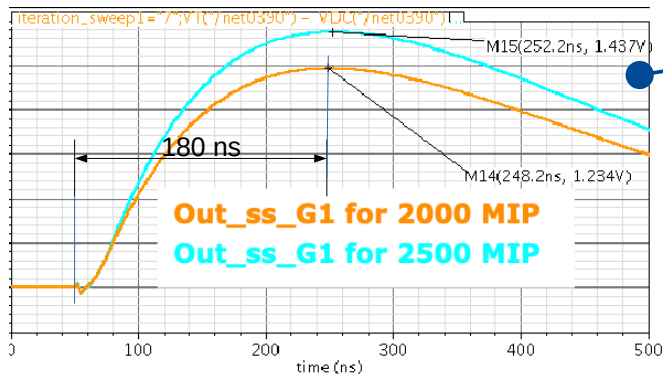
MIP2GeV is extracted from simulation by projected 40 GeV muons perpendicular on the AHCAL tile

- The MIP distribution is fitted with Landau and the position is centered around unity
- The MPV value used as the **MIP2GeV factor**. The value is **481keV/MIP**

# Shaping of the SKIROC2

## Signal path in each channel:

- 1 pre-Amp =
  - integrator with  $\tau_i \sim 0.4\text{--}32 \mu\text{s}$
- Fast Shaper
  - CR-RC<sup>(1~2)</sup> with  $\tau_i$  and  $\tau_d \sim 30\text{--}120 \text{ ns}$
- Slow Shapers
  - CR-RC<sup>(1~2)</sup> with  $\tau_i$  and  $\tau_d = 180 \text{ ns}$

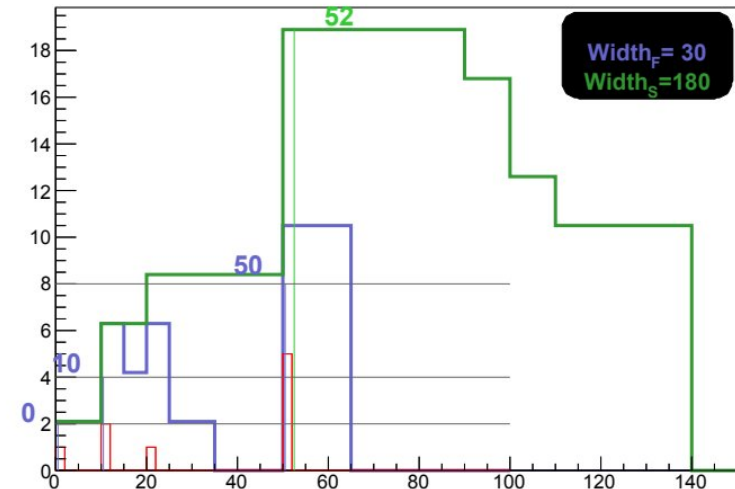
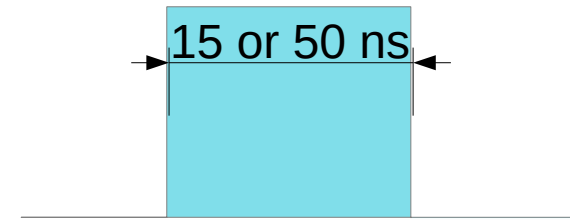


# Scint : Signal shaping

## Simulating Spiroc2E timestamping and energy measurement

- The energy sum of the sub-hits in a cell are integrated over a sliding time window of 50ns
- The 15ns (fast shaper) is introduced to know if the energy deposited in the cell go over threshold
- Then the energy is integrated over 50 ns (slow shaper)
- MIPThr of 0.5 in the ASIC has currently been ignored in this step. Such a cut should be present after all smearing

Equivalent to a «Heaviside shaping»



# SiPM effects

## Ecell / MIPs → Ecell / photon (pixel)

- Using Light Yield values from data
- Cell wise

## Saturation function:

- Smearred with a binomial distribution to model the statistical process of photon detection
  - The number of fired pixels  $p$  is random from  $B(N_{eff} \text{ pixels}, p)$ , which has input parameters:
    - the number of effective pixels of the SiPMs ( $N_{effpixels}$ ) and the probability  $p$  that a pixel is fired

## Additional gaussian smearing:

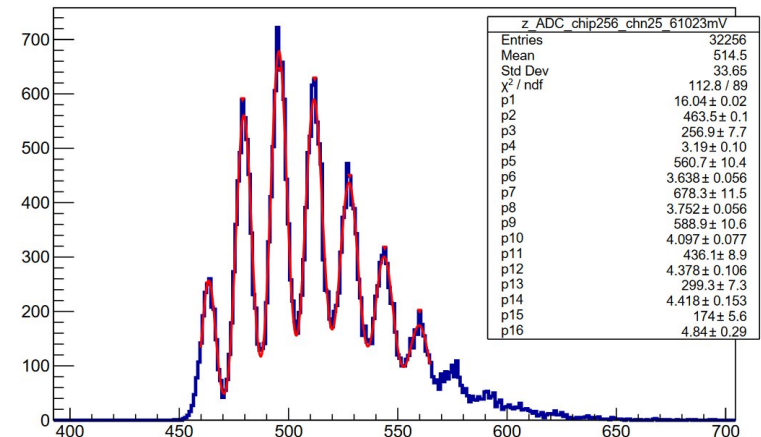
- 0.3 pixels (average value).
- estimated from the width of the pedestal (zero<sup>th</sup> peak in LED measurements)

$$A^{sat}[pixels]_i = N_{effpixels} * (1 - \exp(-\frac{A^{nosat}[pixels]_i}{N_{effpixels}}))$$

Amplitude of the hit not saturated

Saturated amplitude of the hit

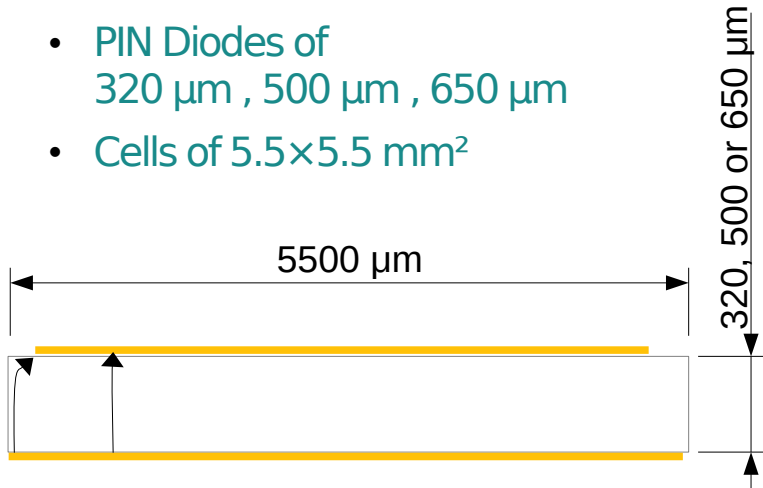
Number of effective pixels, which in our case is 2668 pixels



# Silicon ECAL

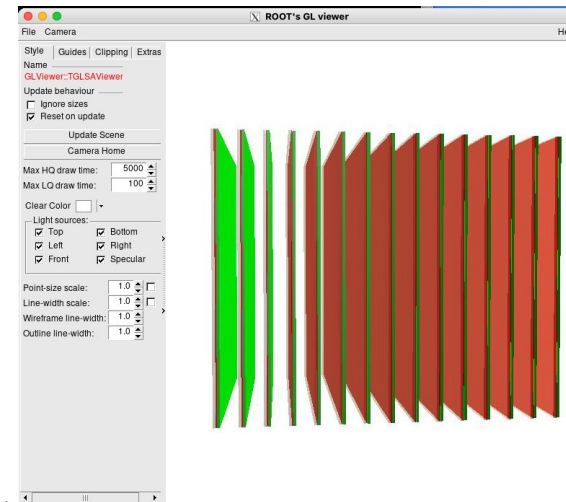
## Prototype:

- 15 layers of  $18 \times 18 \text{ cm}^2$
- Silicon sensors:
  - PIN Diodes of  $320 \mu\text{m}$ ,  $500 \mu\text{m}$ ,  $650 \mu\text{m}$
  - Cells of  $5.5 \times 5.5 \text{ mm}^2$



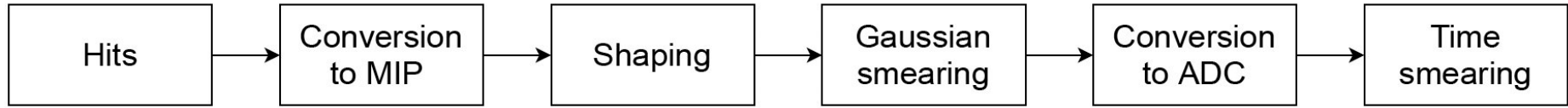
## Simulation

- Gaps between wafers
- No-gaps between cells
  - Charge collections  $\sim 100\%$ 
    - To be evaluated with dedicated simulation (GarField++, ...) and data



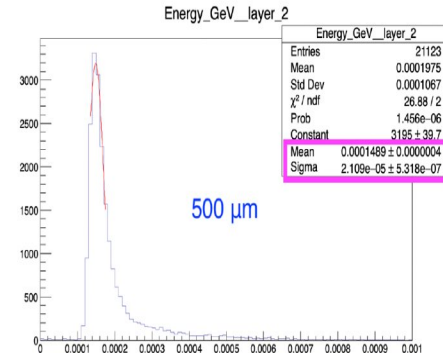
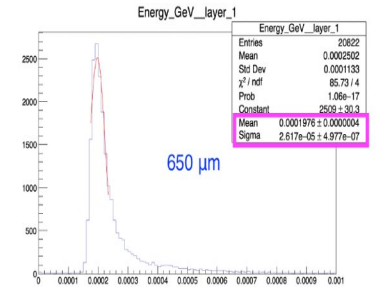
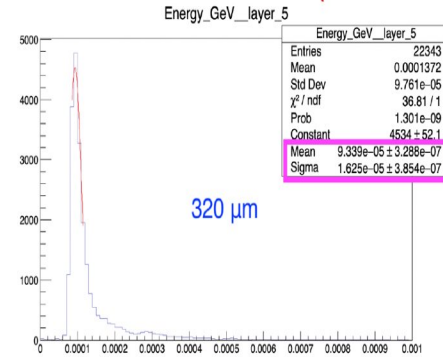


# Silicon ECAL Digi



## Conversion to MIP scale (electrons @ 3 GeV)

- Hits: starting point from raw simulation.
- Map energy deposited to MIP scale.



- Conversion per layer (different layers Si thickness)

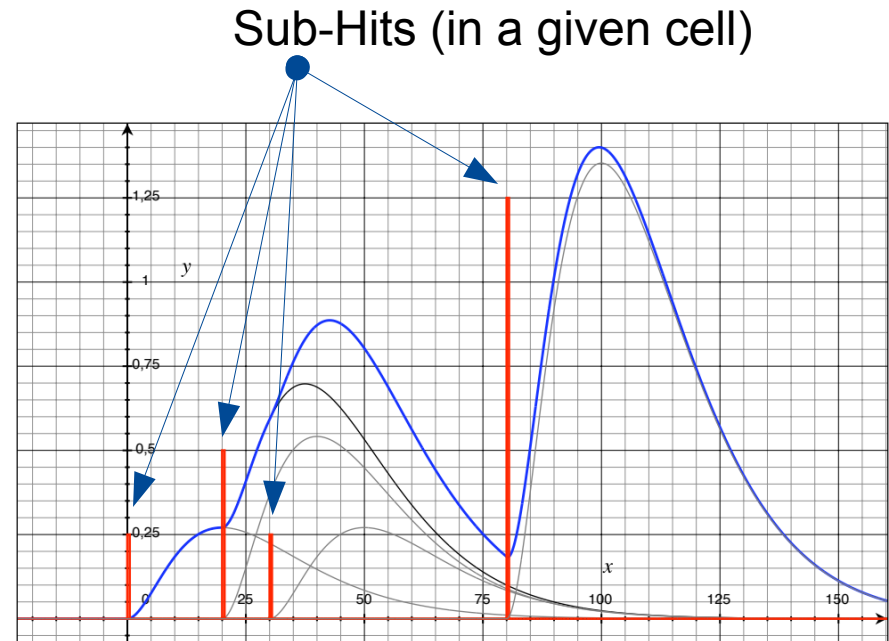
# Pulse shaping

## $n^{\text{th}}$ order CR-RC filter

- Linear response to step function

$$s(t,A)=\begin{cases} 0 & x-t < 0 \\ \frac{A}{n!} \left( \frac{x-t}{\tau_i} \right)^n \exp\left(-\frac{x-t}{\tau_i}\right) & x-t > 0 \end{cases}$$

- Ignores exp. tail
- Ignores saturation effects ( $\geq \sim 2000$  mips)



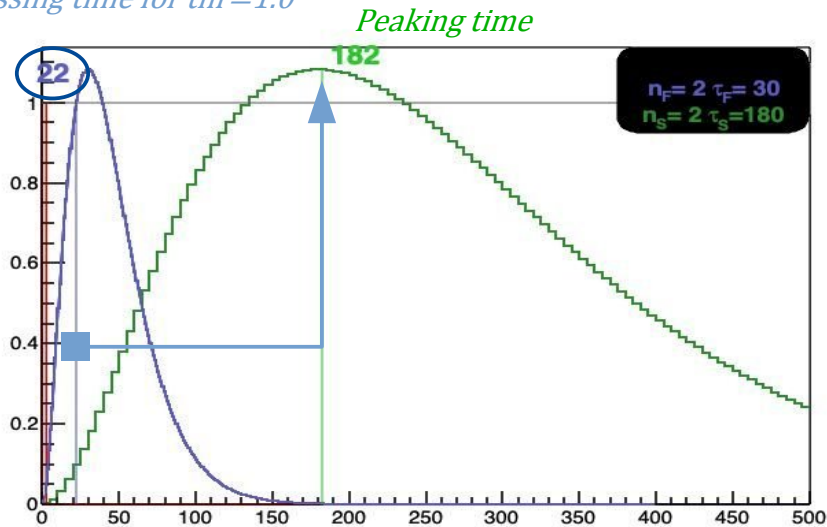
Example of pulse shape output of CR-(CR)<sup>2</sup> filter with a  $n\tau=20$  ns from 4 inputs, at 0, 20, 30 and 80 ns, with relative amplitudes of 1, 2, 1 and 5.

# Implementation for each channel

## Shaping by histograms:

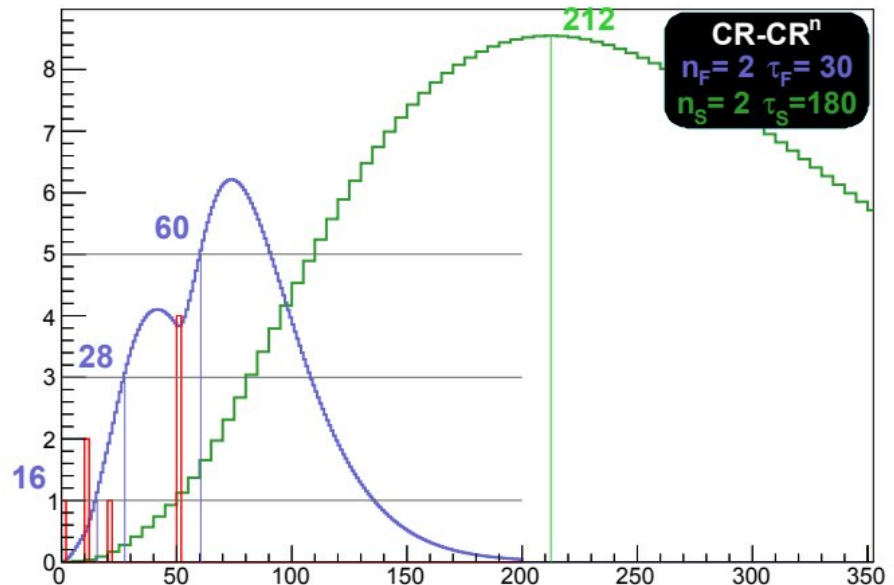
- bin  $\sim$  time resolution
  - 1 ns for FS
  - 5 ns for SS

*Crossing time for thr=1.0*



## Multiple hits

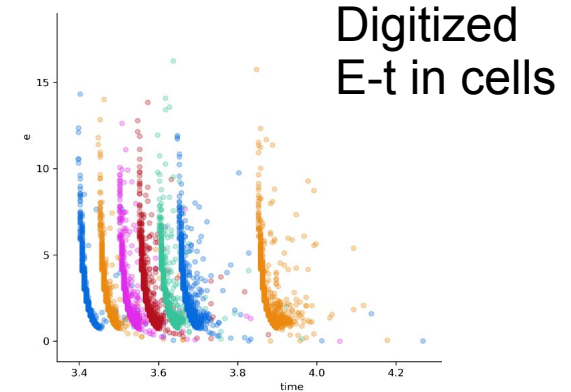
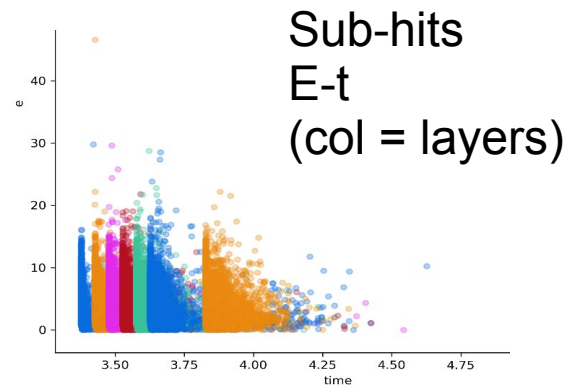
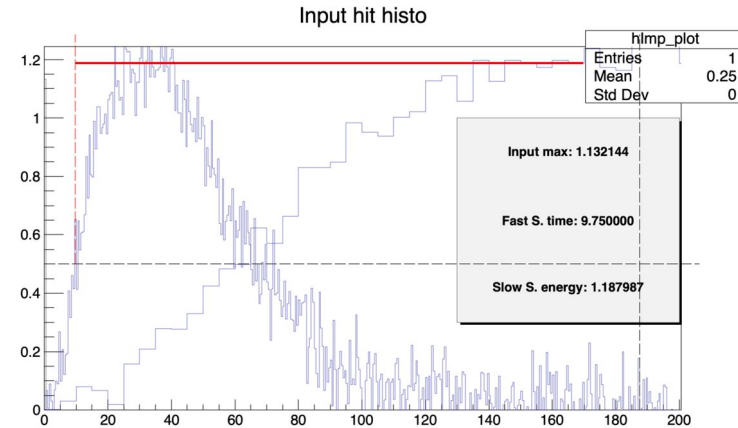
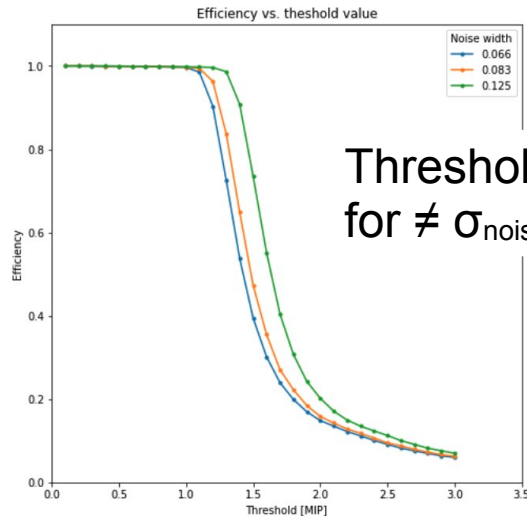
- Time slew effect
- Peaking time



# SiW-ECAL digitizer by shaping

## SiW-ECAL digitizer by shaping

- Shaping processor properly implements noise and a realistic time binning  
Example: Threshold 0.5 MIP, delay 180 ns
- Shapers with noise MIP/12 and MIP/20



# Conclusions

## Summary

- Digitization links MC to exp. Data
- Very sensor Specific
  - Silicon < Scint ≪ Gas RPC
  - Amplitude, Time
  - Geometry
- Electronics :
  - Standard: Gain,
  - Next / On-going precision timing
- Precision of description
  - Gaps, ineff. maps
- Only possible with (lot of) dedicated BT data

## Big, Cursed & politically sensitive work

- The more advanced, the less performant
- Simplistic / Incomplete digitization yields better results... until compared with data !
  - Why invest ?

**→ Technology comparisons review committee task must be done with prototypes & Sim+Digi.**

# Signal collection in Silicon

**See presentation on W. Riegler's presentation**

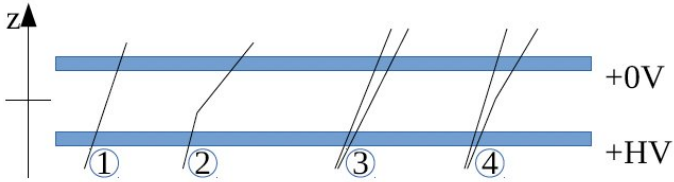
## **Programs:**

- Garfield / Garfield ++
  - Finite Element Electrostatic calculations  
ESIPAP'2021 paper
- Magboltz and Heed
  - Heed ionisation :  
<https://arxiv.org/abs/physics/9912042>
- AllPix<sup>2</sup> (Strasbourg's VTX people)
  - On-going PhD of Elio SACCHETTI (IPHC):
    - Framework with  
GEANT4
    - + Charge propagation
    - + Spice simulation of ASIC

## **First task:**

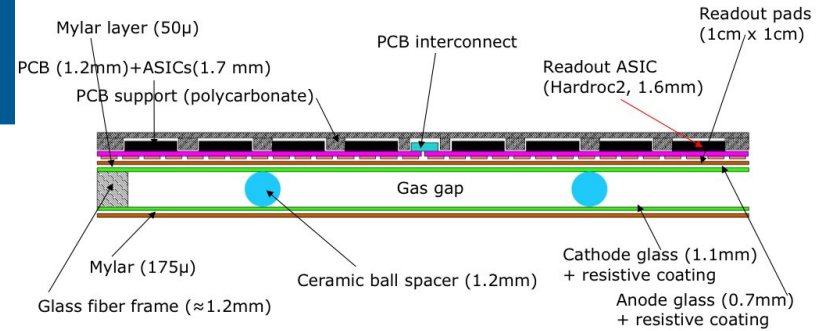
- Get the  $\bar{E}$  field (ie.e doping profile)

# Extras



## Simulation output

- steps list inside RPC gas gaps
- deposited energy from these steps
- occurrence time of each step
- entrance and exit point positions of each step

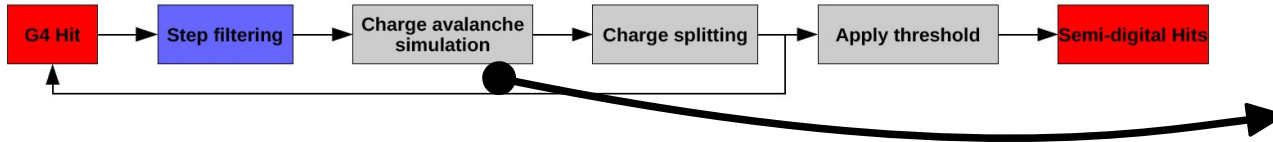


## Glass resistive plate chambers

- Glass electrodes separated by 1.2 mm gas gap
- Glass resistivity  $\approx 10^{12} \Omega m$
- Gas mixture : 93%  $TFE$ , 5%  $CO_2$ , 2%  $SF_6$
- High voltage : 6.9 kV  $\rightarrow$  avalanche mode
- Transverse segmentation : 1  $cm^2$
- Thresholds : 0.114, 5.0, 15.0 pC

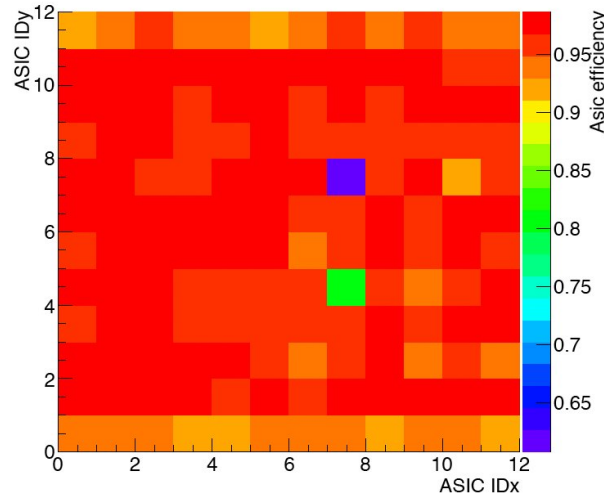


## Digitizer method



### Step filtering

- Step occurrence time < 1000 ns
- Step length > 1  $\mu m$
- Efficiency map
- Charge screening ( $d_{cut}$  tuned with electromagnetic showers)



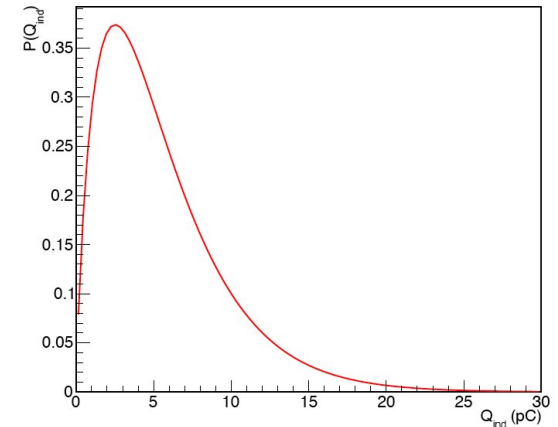
### Charge avalanche simulation

- Charge randomly chosen in Polya distribution :

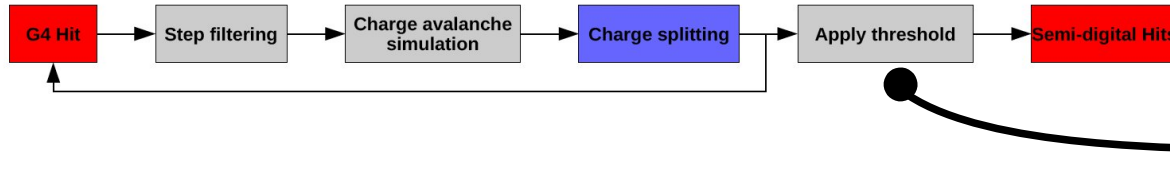
$$P(q) = \frac{1}{\Gamma(\delta + 1)} \left( \frac{1 + \delta}{\bar{q}} \right)^{\delta+1} q^{\delta} e^{-\frac{q}{\bar{q}}(1+\delta)}$$

- Length charge correction :

$$Q_{Corrected} = \begin{cases} Q_{ind} \left( \frac{d_s}{d_{gap}} \right)^{\kappa} & \text{if } \frac{d_s}{d_{gap}} > 1 \\ Q_{ind} & \text{otherwise} \end{cases}$$



# SDHCAL Digi : Amplification



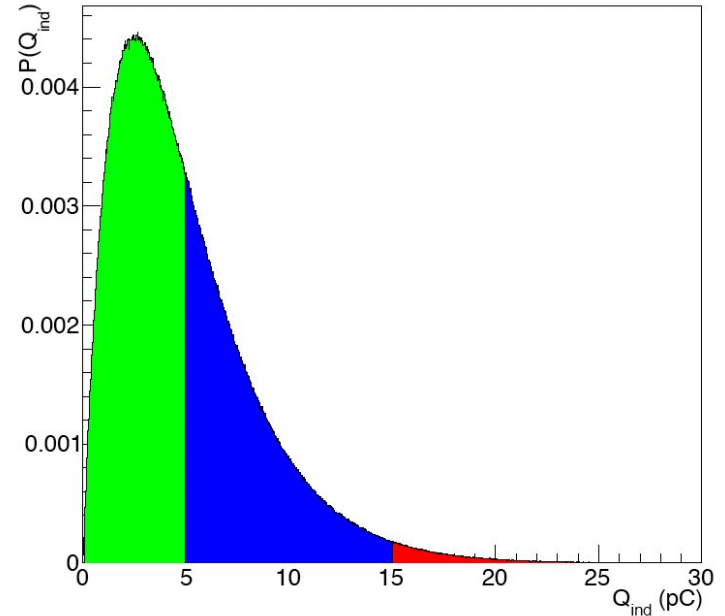
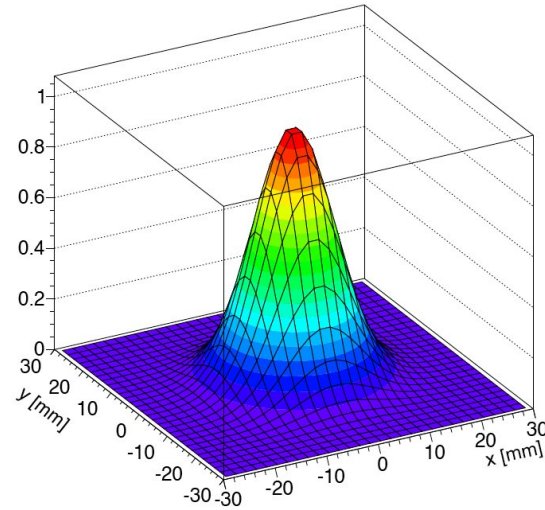
**Thresholds**

- Thresholds 2 and 3 tuned with muon data to reproduce efficiency related to threshold 2 and 3

**Charge spreading**

$$R_i = \frac{\int_{a_i}^{b_i} \int_{c_i}^{d_i} \sum_{j=0}^n \alpha_j e^{-\frac{(x_0-x)^2+(y_0-y)^2}{\sigma_j^2}} dx dy}{N}$$

- Charge in pad  $i$  incremented by  $R_i Q_{corrected}$



# SDHCAL Digi : Tuning

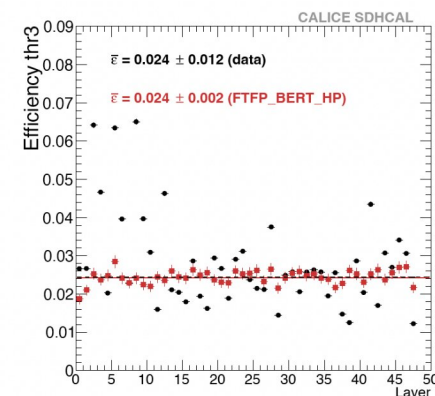
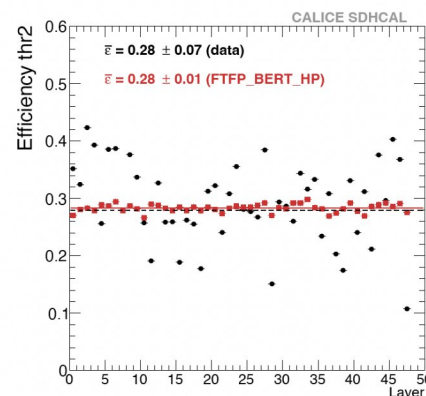
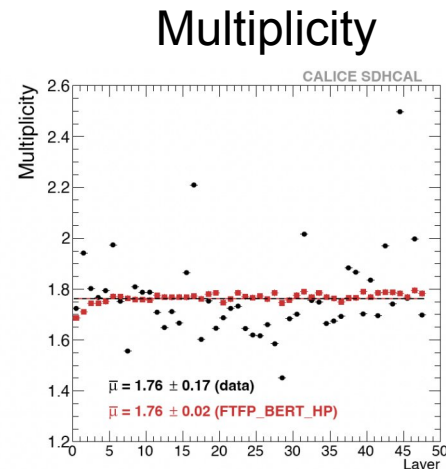
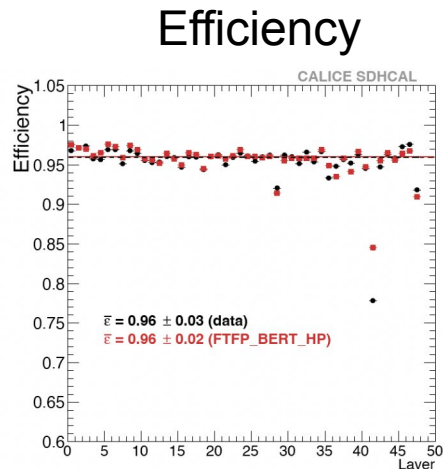
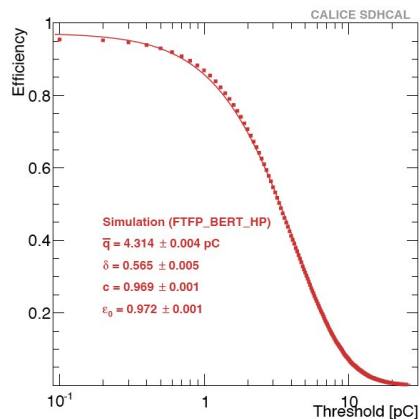
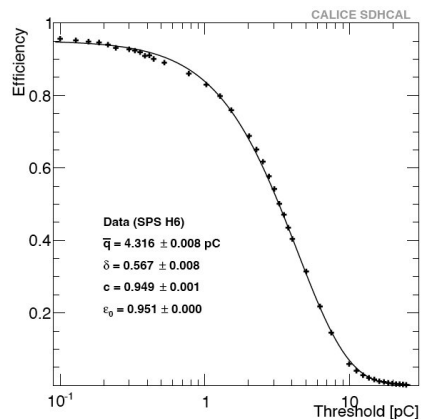
## Digitizer parametrisation : threshold scan

Threshold scan method :

- $\sim 20$  dedicated muon runs
- Threshold variation in few chambers
- Efficiency reconstructed with tracks from other layers
- Fit the curve to extract  $\bar{q}$  and  $\delta$  parameters

$$\epsilon(q) = \epsilon_0 - c \int_0^q P(q') dq'$$

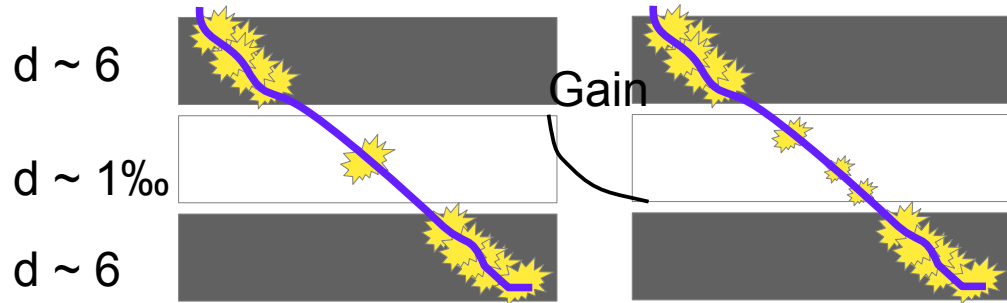
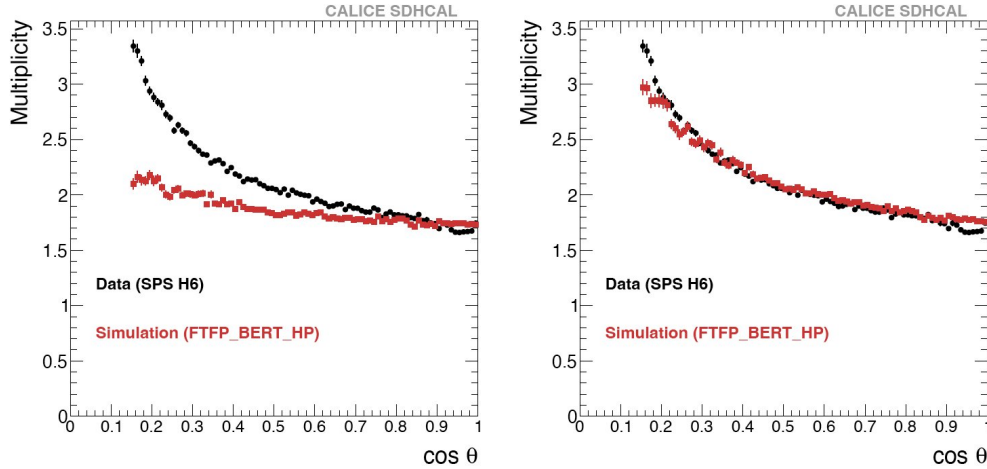
Polya parameter	Digitizer input value
$\bar{q}$	4.58 pC
$\delta$	1.12



Lengthy dedicated BT  $\mu$  runs with thr. scan

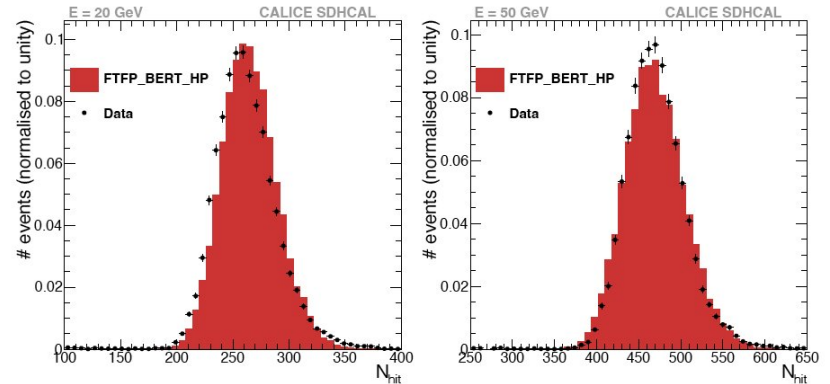
# SDHCAL Digi: results

## Improved parametrization & Step length



## Electromagnetic showers

- Digitizer parameter tuned with EM showers ( $d_{cut}$ )
- EM shower selection :  
 $N_{tracks} = 0$  &  $P_{start} < 5$  &  $N_{layers} < 30$
- Selection efficiency  $\geq 98\%$
- Relative deviation  $< 3\%$



## Comparison with Had. Shower complex:

- Clustering, Shower profiles, Beam contamination ...
- Physics list